

CMUSH2-4
CMUSH2-4A
CMUSH2-4C
CMUSH2-4S
SURFACE MOUNT
ULTRAmi™
SILICON SCHOTTKY DIODES

ULTRAmi™

SOT-523 CASE

CMUSH2-4: SINGLE
CMUSH2-4A: DUAL, COMMON ANODE
CMUSH2-4C: DUAL, COMMON CATHODE
CMUSH2-4S: DUAL, IN SERIES

Central™
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMUSH2-4 Series types are Silicon Schottky Diodes, epoxy molded in a ULTRAmi™ SOT-523 surface mount package, designed for fast switching applications requiring a low forward voltage drop.

MARKING CODE: C42
MARKING CODE: C4A
MARKING CODE: C4C
MARKING CODE: C4S

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Peak Repetitive Reverse Voltage
Continuous Forward Current
Peak Repetitive Forward Current
Forward Surge Current, $t_p=10\text{ms}$
Power Dissipation
Operating and Storage
Junction Temperature
Thermal Resistance

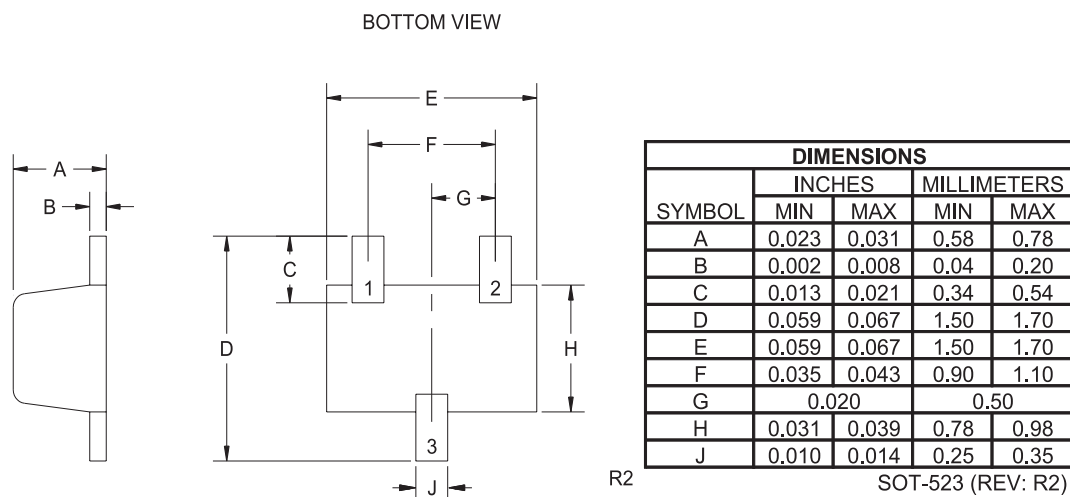
SYMBOL		UNITS
V_{RRM}	40	V
I_F	200	mA
I_{FRM}	300	mA
I_{FSM}	600	mA
P_D	250	mW
T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
Θ_{JA}	500	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS PER DIODE: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_R	$V_R=35\text{V}$		170	500	nA
I_R	$V_R=35\text{V}, T_A=100^\circ\text{C}$		25	100	μA
BV_R	$I_R=100\mu\text{A}$	40	55		V
V_F	$I_F=100\mu\text{A}$		240	260	mV
V_F	$I_F=500\mu\text{A}$		285	310	mV
V_F	$I_F=1.0\text{mA}$		305	330	mV
V_F	$I_F=50\text{mA}$		535	600	mV
V_F	$I_F=100\text{mA}$		670	750	mV
C_T	$V_R=1.0\text{V}, f=1\text{MHz}$			10	pF
t_{rr}	$I_F=I_R=10\text{mA}, I_{rr}=1.0\text{mA}, R_L=100\Omega$			5.0	ns

R0 (31-January 2005)

SOT-523 CASE - MECHANICAL OUTLINE



PIN CONFIGURATION

